

650V 0.135Ω Super Junction Power MOSFET

Description

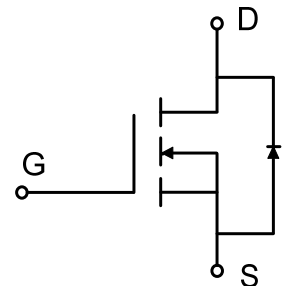
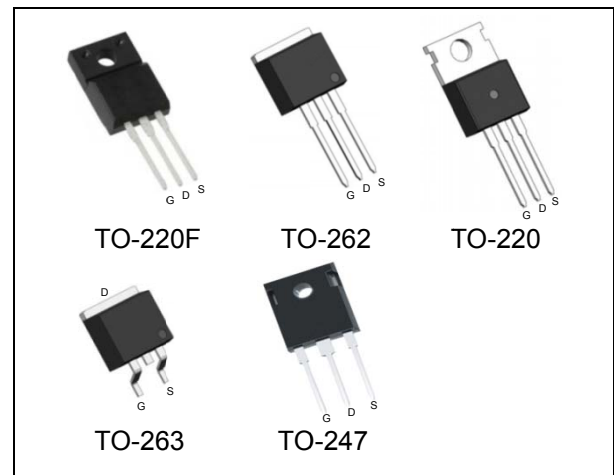
WMOS™ EM is Wayon's 3rd generation super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ EM is suitable for applications which require superior power density and outstanding efficiency.

Features

- $V_{DS} = 700V @ T_{j,max}$
- Typ. $R_{DS(on)} = 0.135\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server



Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Drain-source voltage	V_{DSS}	650		V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$)	I_D	27		A
		16		A
Pulsed drain current ²⁾	I_{DM}	100		A
Gate-source voltage	V_{GS}	± 30		V
Avalanche energy, single pulse ³⁾	E_{AS}	418		mJ
Avalanche energy, repetitive ²⁾	E_{AR}	0.8		mJ
Avalanche current, repetitive ²⁾	I_{AR}	4.5		A
Power dissipation ($T_C = 25^\circ C$) - Derate above $25^\circ C$	P_D	210	34	W
		1.68	0.27	W/ $^\circ C$
Operating and storage temperature range	T_{j}, T_{stg}	-55 to +150		$^\circ C$
Continuous diode forward current ¹⁾	I_S	27		A
Diode pulse current ²⁾	$I_{S,pulse}$	100		A

Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.6	3.6	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=0.25\text{ mA}$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{ mA}$	2	3	4	V
Drain cut-off current	I_{DSS}	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	1	μA
Gate leakage current, forward	I_{GSSF}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Gate leakage current, reverse	I_{GSSR}	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=6\text{ A}$ $T_j = 25^\circ\text{C}$	-	0.135	0.16	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V},$	-	1910	-	pF
Output capacitance	C_{oss}	$f = 1\text{ MHz}$	-	62	-	
Reverse transfer capacitance	C_{rss}		-	3.7	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 300\text{ V}, I_D = 10\text{ A}$	-	40	-	ns
Rise time	t_r	$R_G = 25\Omega, V_{GS}=10\text{ V}$	-	43	-	
Turn-off delay time	$t_{d(off)}$		-	130	-	
Fall time	t_f		-	41	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=480\text{ V}, I_D=10\text{ A},$	-	9.2	-	nC
Gate to drain charge	Q_{gd}	$V_{GS}=0\text{ to }10\text{ V}$	-	18	-	
Gate charge total	Q_g		-	42	-	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=6\text{ A}$	-	-	1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}, I_F=10\text{ A},$	-	310	-	ns
Reverse recovery charge	Q_{rr}	$di_f/dt=100\text{ A}/\mu\text{s}$	-	3.8	-	μC
Peak reverse recovery current	I_{rrm}		-	29	-	A

Notes:

- Limited by $T_{j\text{max}}$. Maximum duty cycle $D=0.5$.
- Pulse width limited by maximum junction temperature.
- $I_{AS} = 3.4\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\Omega$, starting $T_j = 25^\circ\text{C}$.

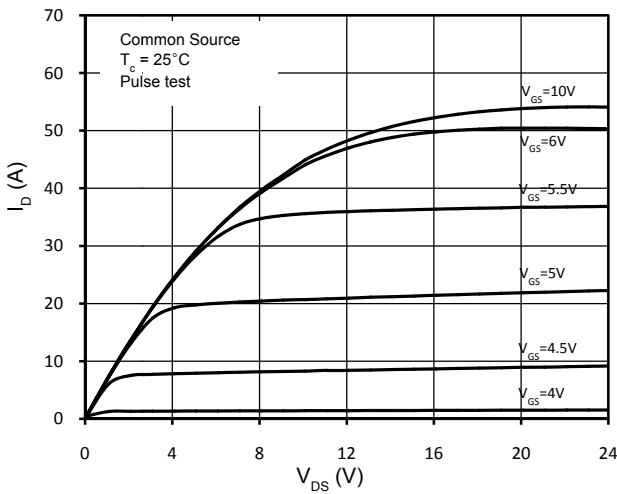


Figure 1. On-Region Characteristics

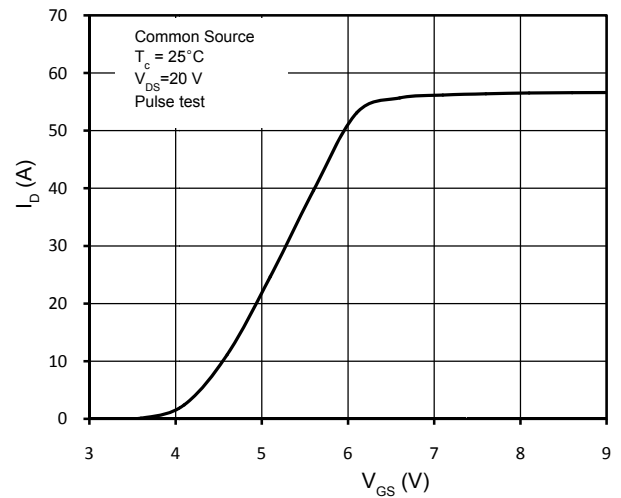


Figure 2. Transfer Characteristics

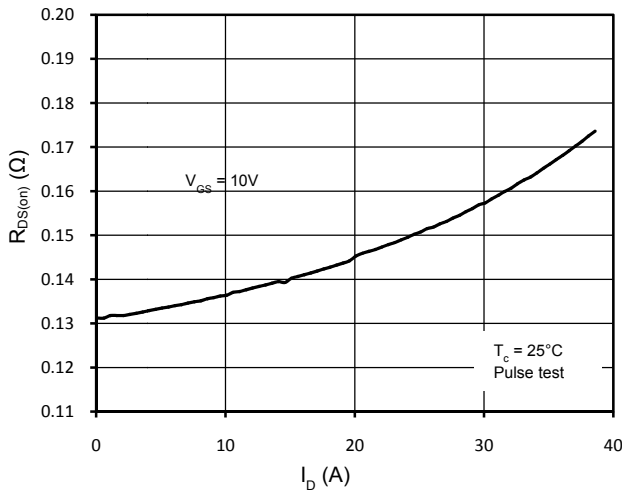


Figure 3. Static Drain-Source On Resistance

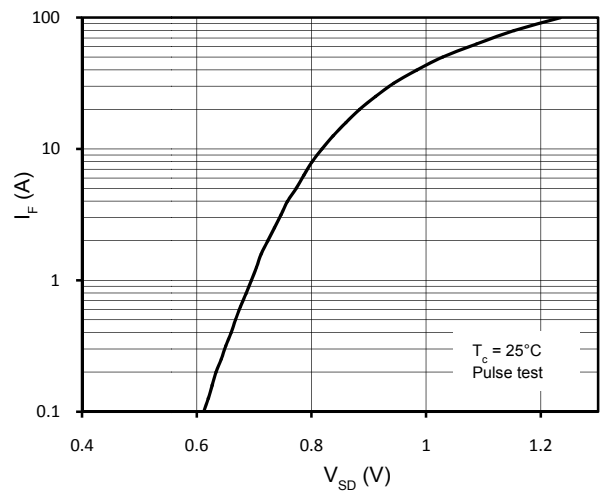


Figure 4. Body-Diode Forward Characteristics

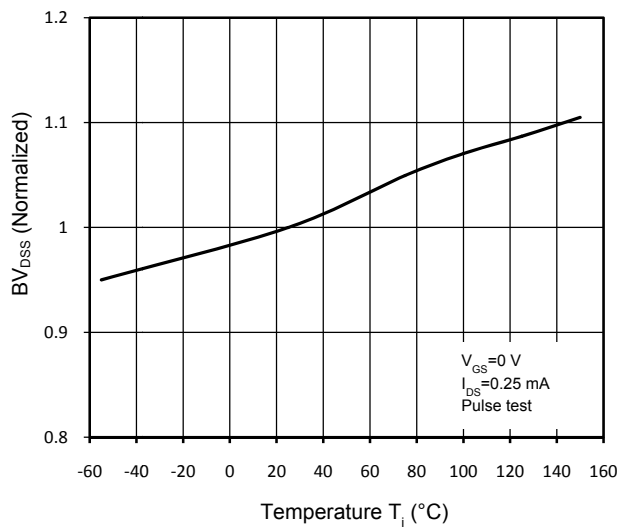


Figure 5. Normalized $BV_{DS(s)}$ vs. Temperature

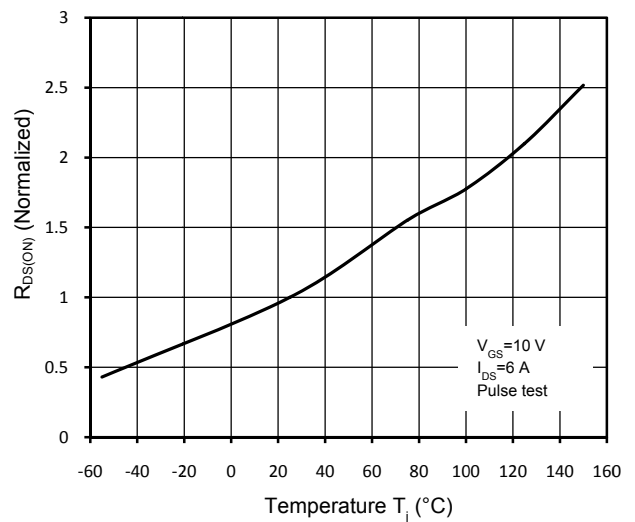


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

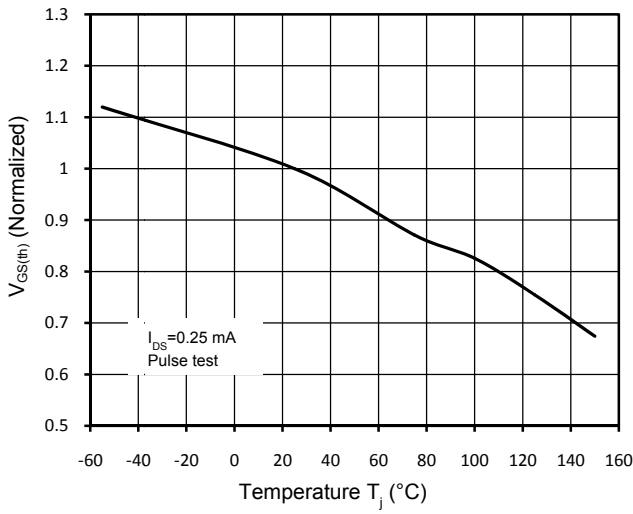


Figure 7. Threshold Voltage vs. Temperature

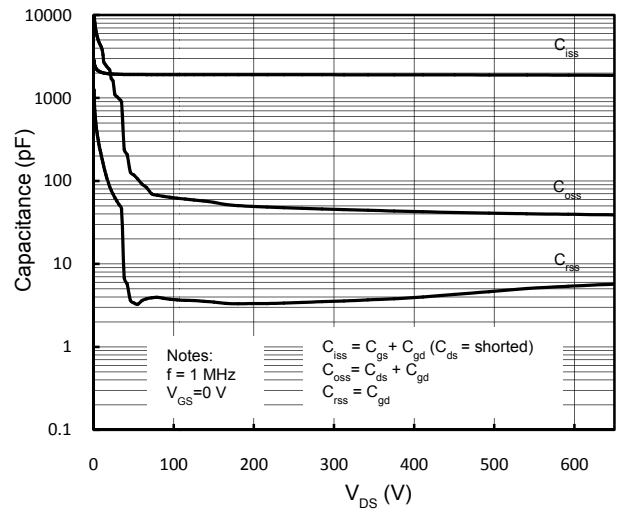


Figure 8. Capacitance Characteristics

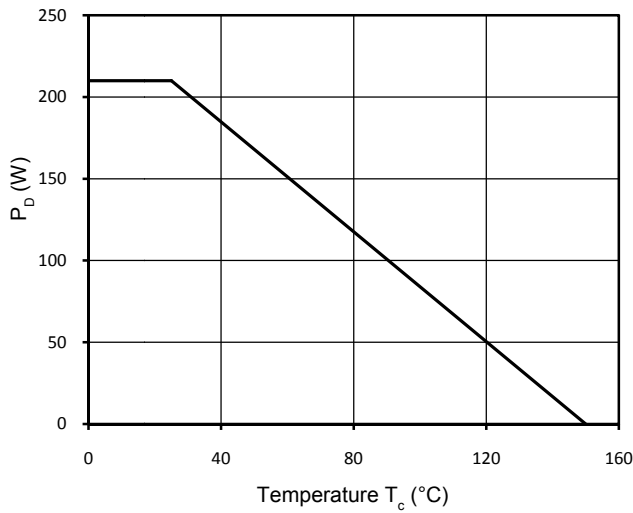


Figure 9. Power Dissipation

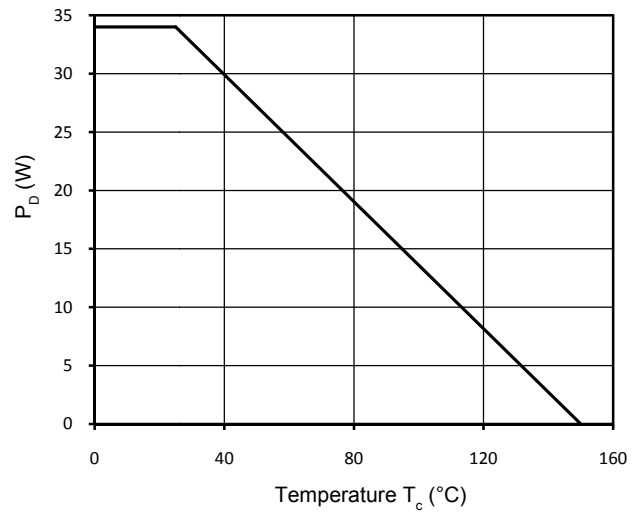


Figure 10. Power Dissipation (TO-220F)

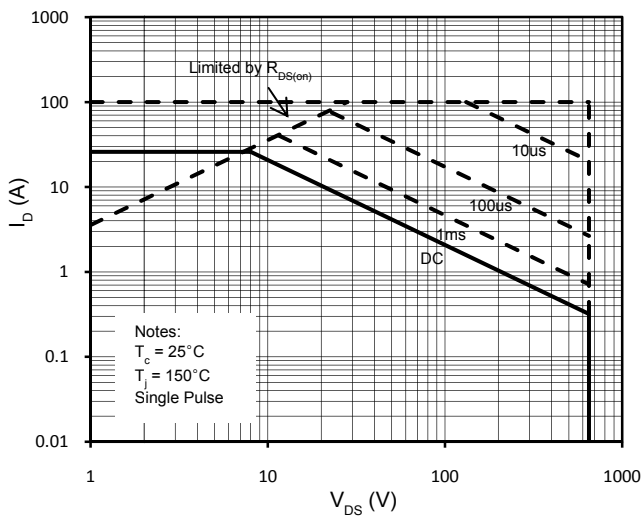


Figure 11. Maximum Safe Operating Area

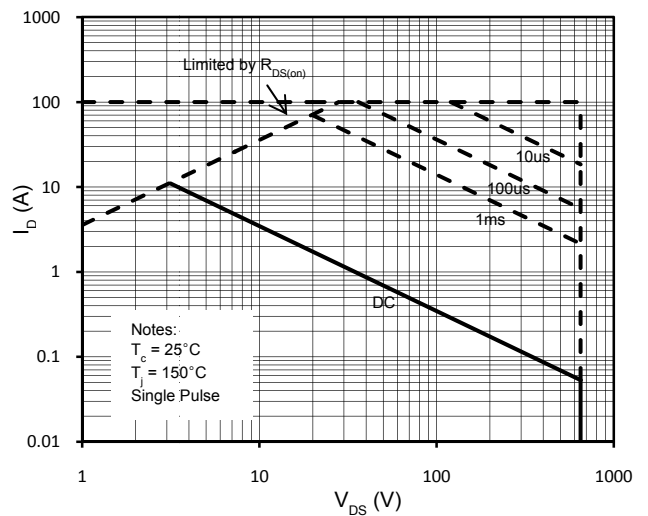


Figure 12. Maximum Safe Operating Area (TO-220F)

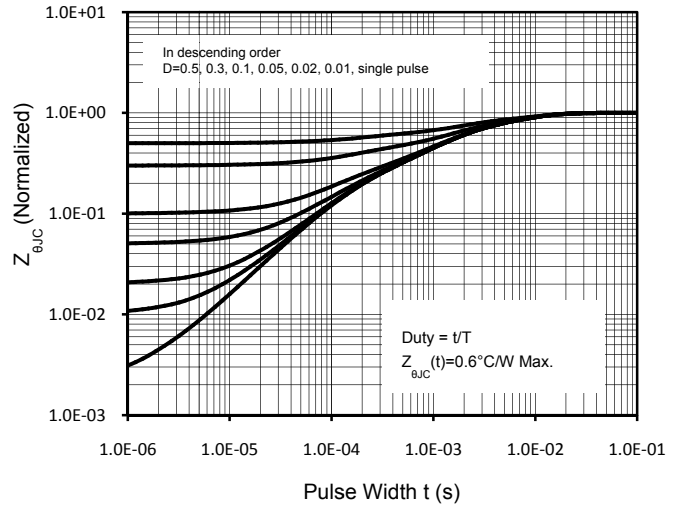
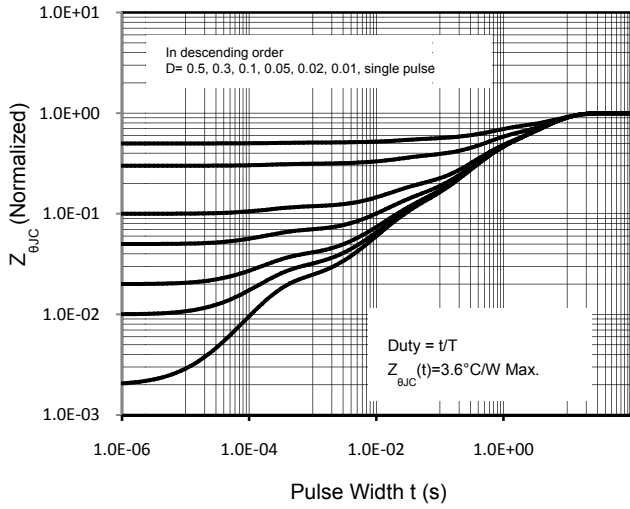


Figure 13. Transient Thermal Response Curve (TO-220F) Figure 14. Transient Thermal Response Curve

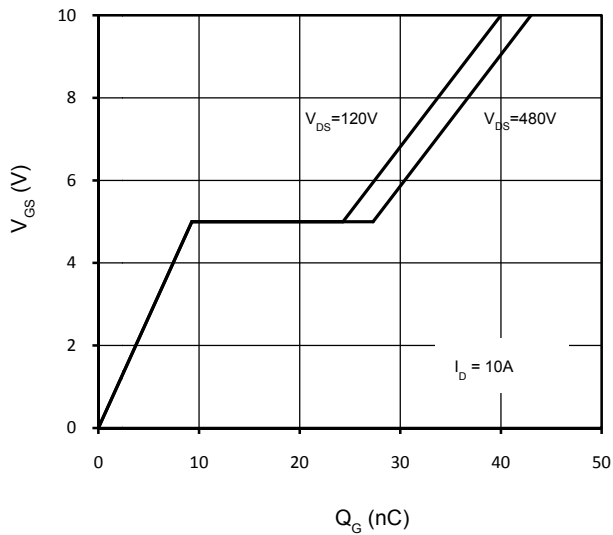


Figure 15. Gate Charge Characteristics

Gate Charge Test Circuit & Waveform



Switching Test Circuit & Waveforms

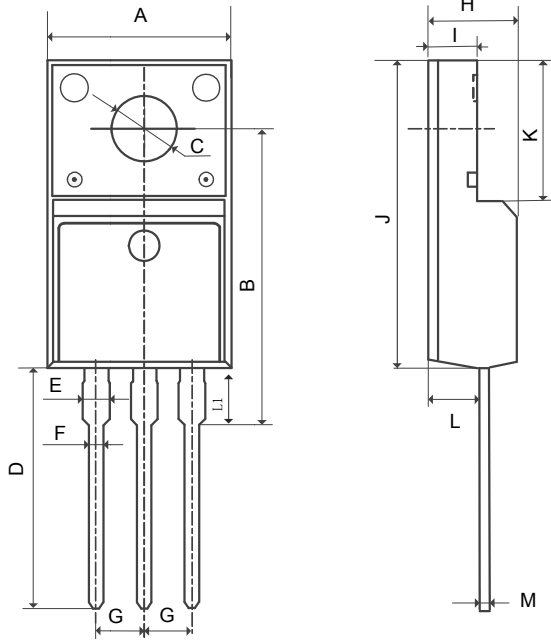


Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-220F

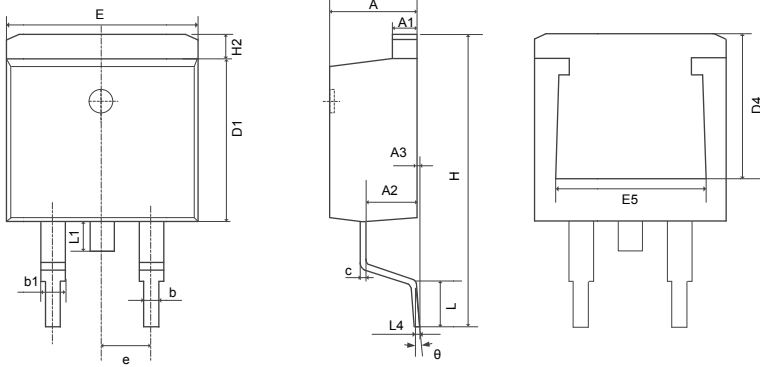
COMMON DIMENSIONS



SYMBOL	MM		
	MIN	NOM	MAX
A	9.96	10.16	10.36
B	15.10	15.60	16.10
C	3.03	3.20	3.38
D	12.64	12.96	13.28
E	1.18	1.38	1.58
F	0.70	0.81	0.95
G	2.54REF		
H	4.50	4.70	4.90
I	2.34	2.54	2.74
J	15.57	15.87	16.17
K	6.70REF		
L	2.56	2.76	2.96
M	0.40	0.52	0.65
L1	2.85	3.10	3.45

Mechanical Dimensions for TO-263

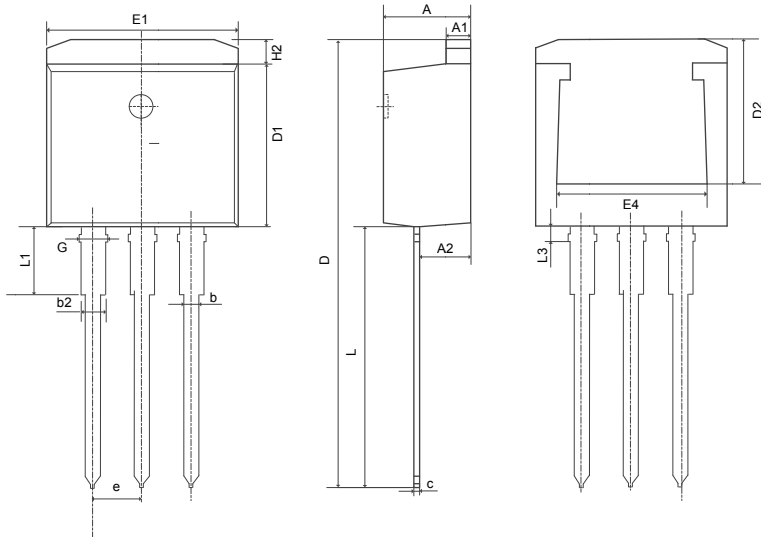
COMMON DIMENSIONS



SYMBOL	MM		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	—	—
E	9.86	10.16	10.36
E5	7.06	—	—
e	2.54BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.3	2.60
L1	1.40	1.55	1.70
L4	0.25BSC		
θ	0°	5°	9°

Mechanical Dimensions for TO-262

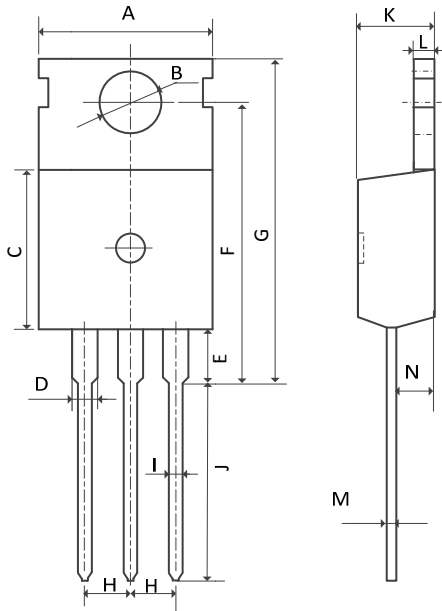
COMMON DIMENSIONS



SYMBOL	MM		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
b	0.71	0.81	0.96
b2	1.17	1.27	1.42
c	0.28	0.38	0.53
D	23.20	23.70	24.02
D1	8.50	8.7	8.90
D2	6.00	—	—
E1	9.86	10.16	10.36
E4	7.06	—	—
e	2.54BSC		
G	1.25	1.35	1.50
H2	—	—	1.50
L	13.33	13.73	14.13
L1	3.50	3.75	4.00
L3	1.28	1.43	1.58

Mechanical Dimensions for TO-220

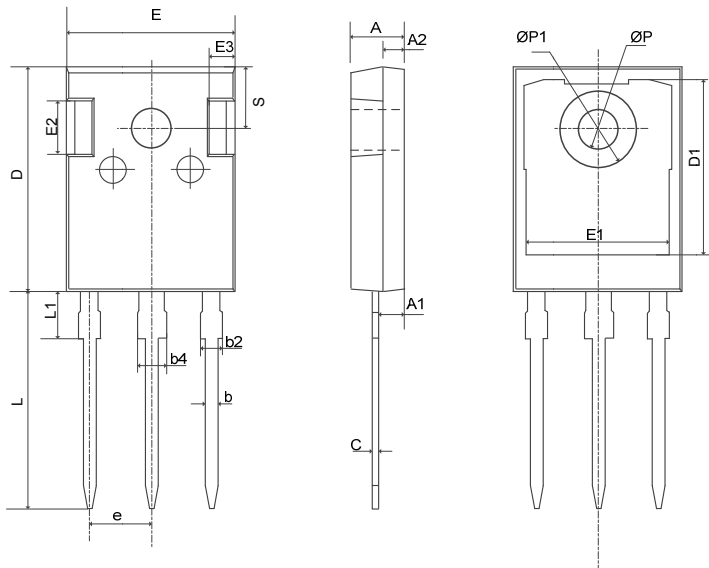
COMMON DIMENSIONS



SYMBOL	MM		
	MIN	NOM	MAX
A	9.70	10.00	10.20
B	3.40	3.60	3.80
C	8.90	9.10	9.40
D	1.17	1.27	1.47
E	2.60	3.10	3.40
F	15.10	15.80	16.70
G	19.55MAX		
H	2.54REF		
I	0.70	0.80	0.95
J	9.35	10.30	11.00
K	4.30	4.57	4.77
L	1.20	1.30	1.45
M	0.40	0.50	0.65
N	2.20	2.40	2.60

Mechanical Dimensions for TO-247

COMMON DIMENSIONS

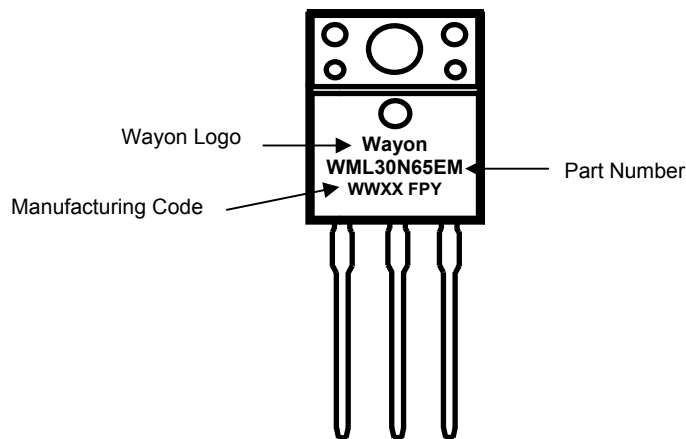


SYMBOL	MM		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.60
E3	2.10	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	—	—	4.30
ØP	3.40	3.60	3.80
ØP1	—	—	7.30
S	6.15BSC		

Ordering Information

Part	Package	Marking	Packing method
WML30N65EM	TO-220F	WML30N65EM	Tube
WMK30N65EM	TO-220	WMK30N65EM	Tube
WMN30N65EM	TO-262	WMN30N65EM	Tube
WMM30N65EM	TO-263	WMM30N65EM	Tape and Reel
WMJ30N65EM	TO-247	WMJ30N65EM	Tube

Marking Information



Contact Information

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WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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